Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 600 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes
- N Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MAC320A8FP, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage ⁽¹⁾ (T _J = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open)	V _{DRM} , V _{RRM}	600	Volts
On-State RMS Current (T _C = +75°C, Full Cycle Sine Wave 50 to 60 Hz) ⁽²⁾	I _{T(RMS)}	20	Amps
Peak Non-Repetitive Surge Current (One Full Cycle, 60 Hz, T _C = +75°C, preceded and followed by rated current)	I _{TSM}	150	Amps
Peak Gate Power $(T_C = +75^{\circ}C, \text{ Pulse Width} = 2 \mu\text{s})$	Рам	20	Watts
Peak Gate Voltage $(T_C = +75^{\circ}C, \text{ Pulse Width} = 2 \mu\text{s})$	V _{GM}	10	Volts
Average Gate Power (T _C = +75°C, t = 8.3 ms)	P _{G(AV)}	0.5	Watt
Peak Gate Current (T _C = +75°C, Pulse Width = 2 μs)	1 _{GM}	2.0	Amps
RMS Isolation Voltage (T _A = 25°C, Relative Humidity ≤ 20%) (९১)	V _(ISO)	1500	Volts
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	–40 to +150	°C

- (1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) The case temperature reference point for all TC measurements is a point on the center lead of the package as close as possible to the plastic body.



ON Semiconductor

http://onsemi.com

ISOLATED TRIACs (%) 20 AMPERES RMS 600 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 3

PIN ASSIGNMENT				
1 Main Terminal 1				
2	Main Terminal 2			
3	Gate			

ORDERING INFORMATION

Device	Package	Shipping
MAC320A8FP	ISOLATED TO220FP	500/Box

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.8	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	°C

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_C = 25^{\circ}\text{C unless otherwise noted}; \ \text{Electricals apply in both directions})$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current (V _D = Rated V _{DRM} , V _{RRM} ; Gate Open)	T _J = 25°C	I _{DRM} , I _{RRM}		_	10	μΑ
	$T_{J} = +125^{\circ}C$		_	_	2.0	mA

OFF CHARACTERISTICS

Peak On-State Voltage	V _{TM}	_	1.4	1.7	Volts
(I _{TM} = ±28 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)				0	

ON CHARACTERISTICS

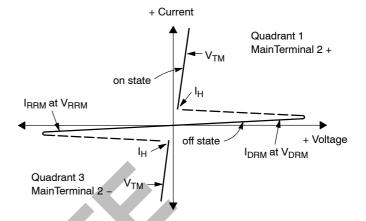
Peak Gate Trigger Current (Main Terminal Voltage = 12 Vdc, R _L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(-)	lgT		11-10-10-10-10-10-10-10-10-10-10-10-10-1	50 50 50 75	mA
Peak Gate Trigger Voltage (Main Terminal Voltage = 12 Vdc, R _L = 100 Ohms) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	V _{GT}	ORIM —	0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	Volts
Gate Non-Trigger Voltage (Main Terminal Voltage = 12 V, R_L = 100 Ω , T_J = +110°C) All Four Quadrants	V _{GD}	0.2	_	_	Volts
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = ±200 mA)	lн	_	6.0	40	mA
Turn-On Time $(V_D = \text{Rated V}_{DRM}, I_{TM} = 28 \text{ A}, I_{GT} = 120 \text{ mA}, \\ \text{Rise Time} = 0.1 \ \mu\text{s}, \text{Pulse Width} = 2 \ \mu\text{s})$	t _{gt}	_	1.5	10	μs

DYNAMIC CHARACTERISTICS

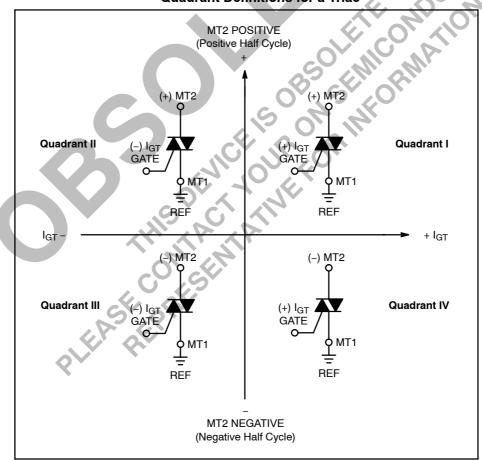
Critical Rate of Rise of Commutation Voltage	dv/dt(c)	_	5.0	_	V/μs
(V _D = Rated V _{DRM} , I _{TM} = 28 A, Commutating di/dt = 10 A/ms,					
Gate Unenergized, $T_C = +75^{\circ}C$					

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I _{DRM}	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V _{TM}	Maximum On State Voltage
I _H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

TYPICAL CHARACTERISTICS

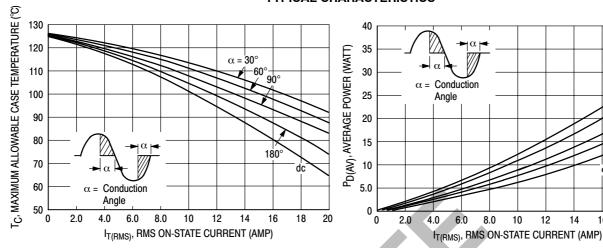


Figure 1. RMS Current Derating

Figure 2. On-State Power Dissipation

90°

16 18

20

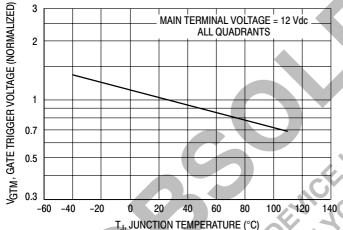


Figure 3. Typical Gate Trigger Voltage

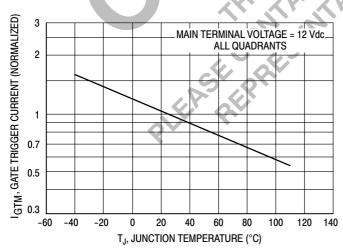


Figure 4. Typical Gate Trigger Current

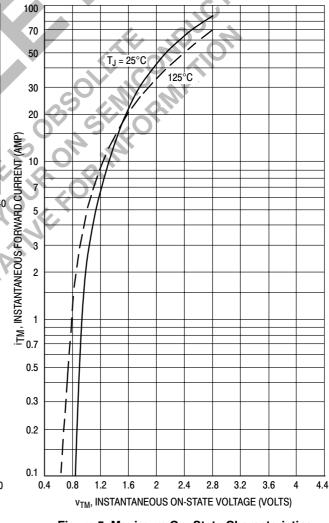


Figure 5. Maximum On-State Characteristics

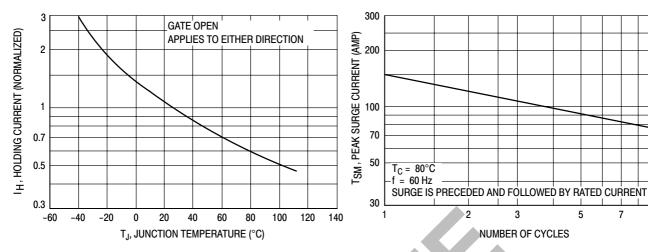
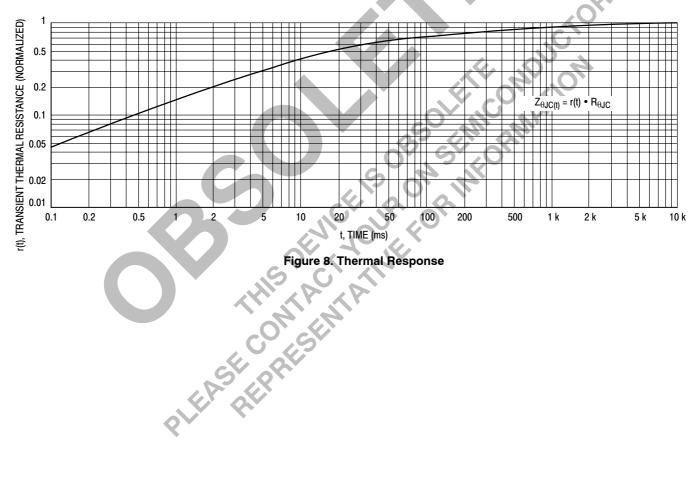


Figure 6. Typical Holding Current

Figure 7. Maximum Nonrepetitive Surge Current

5

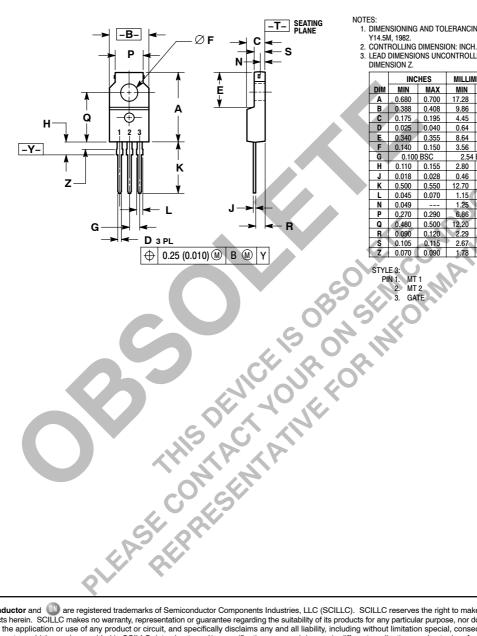
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PACKAGE DIMENSIONS

ISOLATED TO-220 Full Pack

CASE 221C-02 **ISSUE C**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100	BSC	2.54	BSC
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049		1.25	-
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

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